**Biography: Ayayi Claude Ahyi**

**Ayayi Claude Ahyi** received a PhD. Degree in Electrical Engineering from the “Université des Sciences et Technologies de Lille” (France) in 1997. His PhD research on Ultra High Speed Camera Design, Fabrication and Application to Underwater Acoustic Scattering was an interdisciplinary combination of acoustics and electronics. This work resulted in several publications and a patent on an Ultra High Speed Camera.

After graduation he moved to Auburn, Alabama working in Auburn University as a Postdoctoral fellow on both Acoustic Scattering and Organic Semiconductors and Electro-optic modulation.

In 2002 he joined the Solid State Physics group of the Auburn University Physics department as a Post Doctoral fellow. Early work in the Physics Department was focused on SiC Schottky devices, in particular the improvement of their breakdown characteristics using various junction termination extensions. Several studies were also made on the radiation hardness of the devices.

In 2007 Dr. Ahyi became part of the Physics Department faculty as an Assistant Research Professor. He is now an Associate Research Faculty. His current work is focused on Wide bandgap MOSFET interfaces, with an accent on SiC MOSFET. Since he joined the department Dr. Ahyi has been co-recipient of two patents, one on SiC impurity doping and the second on SiC MOS interface improvement.